

GS302SA-3 Programmable Linear Hall-Effect IC

- GaAs + Si Hybrid Programmable Linear Hall-Effect IC
- Single power supply : VDD 3V ~ 5.5V
- Analog Fixed or Ratiometric Output
- Wide ambient Temperature Range : Ta -40°C ~ 125°C
- Quick response for magnetic field with wide bandwidth
- Programmable via One Wire Interface at Vout Pin

Output Characteristics

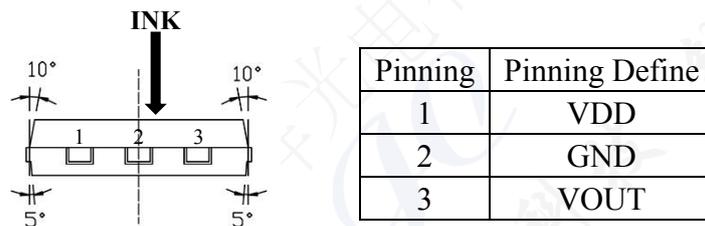


Figure1. Definition of sensitivity direction

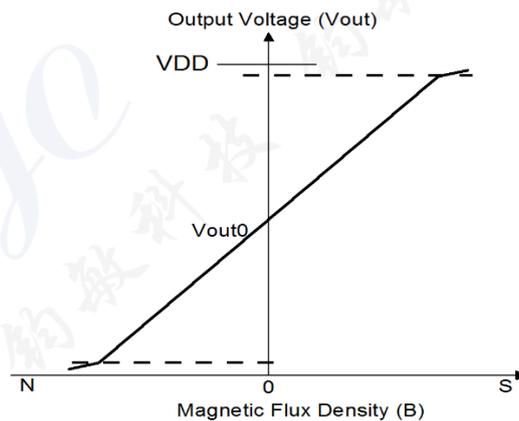
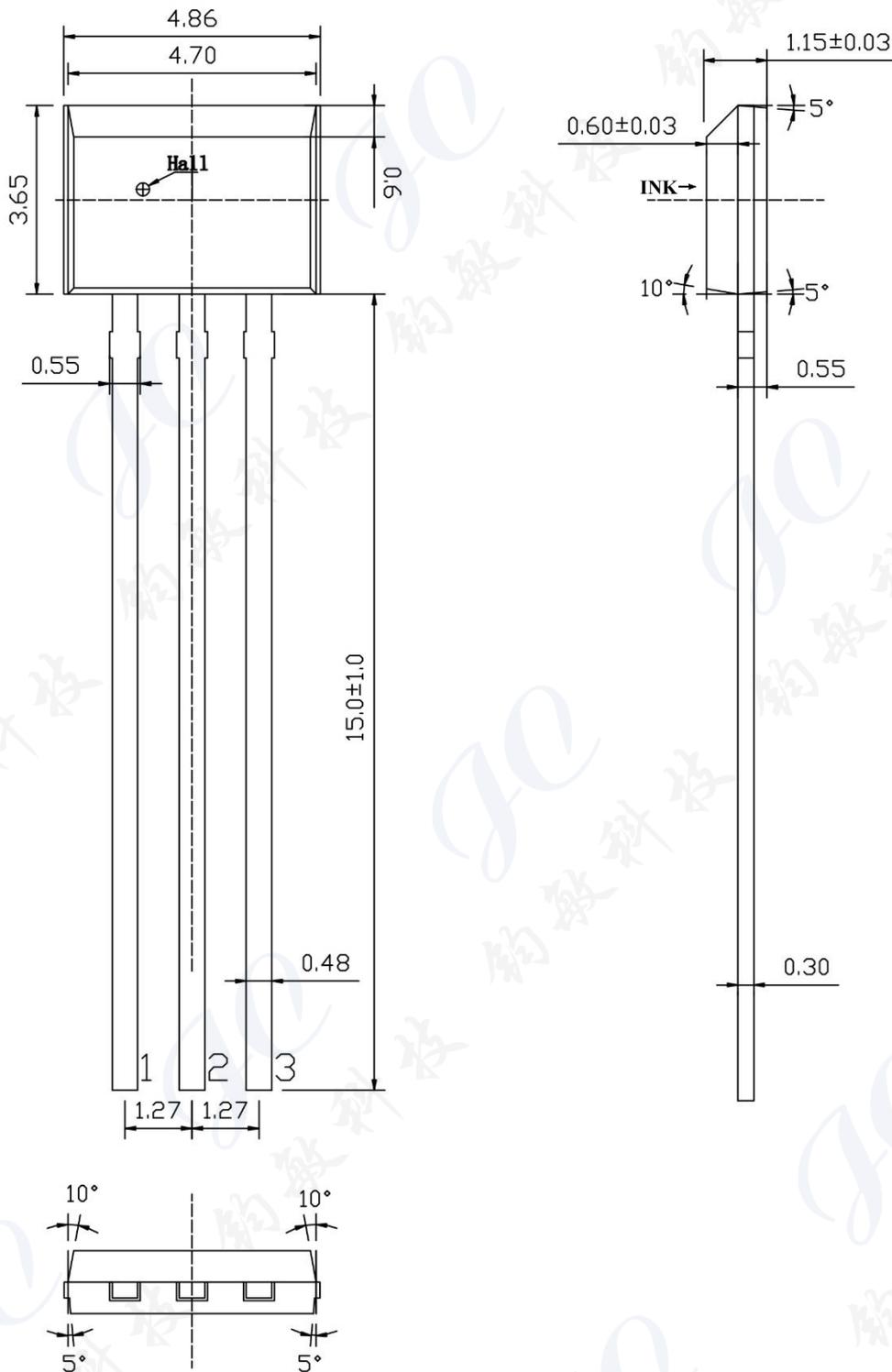


Figure 2. Output Characteristics of GS302SA-3

Dimensional Drawing (Unit MM)



¹Unmarked tolerances are controlled according to $\pm 0.05\text{mm}$ while the angel tolerance is $\pm 1^\circ$.

Absolute Maximum Rating

Table 1 . GS302SA-3 Working conditions

Characteristics	Symbol	Condition	Min	Typ	Max	Unit
Supply Voltage	V_{DD}	$T_a = 25^{\circ}C$	-0.3		6.5	V
Output Current	I_{out}	$T_a = 25^{\circ}C$	-45		45	mA
Analog output	V_{out} / V_{bias}	$T_a = 25^{\circ}C$	0.4		$V_{DD}-0.4$	V
Storage Temp.	T_s		-40		150	$^{\circ}C$
Operation Temp.	T_a		-40		125	$^{\circ}C$

Operation Conditions

Table 2. Electric and magnetic characteristics Ta=-40 to 85°C

Characteristics	Symbol	Condition	Min	Type	Max	Unit
Supply Voltage	V _{DD}	Ta = 25°C	3		5.5	V
Current Consumption	I _s	In Programming @ Ta = 25°C			33	mA
		In normal operation @Ta=25°C		6.5	11	mA
Sensitivity Range	V _{hrange}	Ta = 25°C	0.5		200	mV/mT
Response Time	T _r	M1 C _{load} =20pF			3	μs
Signal bandwidth	B _w			250	500	KHz
Load Capacitance	C _L	Ta = 25°C		20p	1n	F
Bias Voltage	V _{bias}	Ta = 25°C	2.490		2.510	V
Quiescent Voltage of Differential Output at Ta 25°C	V ₀ -V _{bias}	M1	-0.01		0.01	V
Quiescent Voltage of Differential Output In -40°C~85°C	V ₀ -V _{bias}	M1	-0.02		0.02	V
Quiescent Voltage (fixed output) Ta=25°C	V ₀	M1	2.490		2.510	V
Quiescent Voltage (fixed output) In -40°C~85°C	V ₀	M1	2.480		2.520	V
Sensitivity drift through temperature (fixed output)	ΔS/S(25°C)	M1 In -40°C~25°C	-1.5		1.5	%
		M1 In 25°C~85°C	-1.5		1.5	%
Output Saturation Voltage	V _{out-SatH}		V _{DD} -0.5			V
	V _{out-SatL}				0.5	V
Error of sensitivity (rationmetric output) In -40°C~85°C	S _{erro}	V _{DD} in range 4.75~5.25V	-0.4		0.4	%
Error of Quiescent Voltage (rationmetric output) In -40°C~85°C	V _{0erro}	V _{DD} in range 4.75~5.25V	-0.3		0.3	%
Linearity Error	ρ	M1	-0.5		0.5	%

Note:

 M1 : V_{DD}=5V , V₀=2.500V or V_{bias} , V_{out} = V₀±2.000V@±20mT , sensitivity : 10 mV/GS ;

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Characteristics Definitions

1. Sensitivity V_{hrange} [mv/mT].

Sensitivity is defined as the slope of the approximate straight line calculated by the least square method, using data of OUT voltage (V_{out}) when the magnetic flux density (B) is swept within the range of input magnetic flux density (B_{in}).

2. Linearity Error ρ [%F.S.].

Linearity error is defined as the ratio of the maximum perpendicular deviation (MPD) to the full scale (F.S.), where MFD is the maximum difference between the OUT voltage (V_{out}) and the approximate straight line calculated in the sensitivity definition. Definition formula is shown in below:

$$\rho = 100 * \frac{\text{MFD}}{\text{F.S.}} = 100 * \frac{\text{MFD}}{V_H - V_L}$$

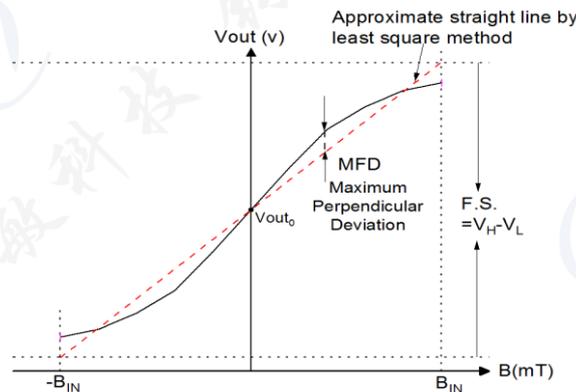


Figure 3. Output characteristics of GS302SA-3

3. Ratiometric output error of sensitivity V_{0erro} [%] and ratiometric output error of Quiescent voltage S_{erro} [%].

The quiescent voltage (V_{out0}) of the GS302SA-3 is constant, which means that it does not vary with the VDD. Error of Quiescent Voltage is defined as the difference between the V_h (or V_{out0}) when the VDD is changed from 5.0v to VDD_1 ($4.75\text{v} < VDD_1 < 5.25\text{v}$ or $4.5\text{v} < VDD_1 < 5.5\text{v}$). Definition formula is shown in blow:

$$S_{\text{erro}} = \left[\frac{V_{\text{out}}(VDD)}{V_{\text{out}}(5\text{v})} - \frac{VDD}{5} \right] * 100$$

$$V_{\text{0erro}} = \left[\frac{V_0(VDD)}{V_0(5\text{v})} - \frac{VDD}{5} \right] * 100$$

4. Rise response time T_r [μs].

Rise response time is defined as the time delay from the 90% of input magnetic field (B) to the 90% of the OUT voltage (V_{out}) under the pulse input of magnetic flux density.

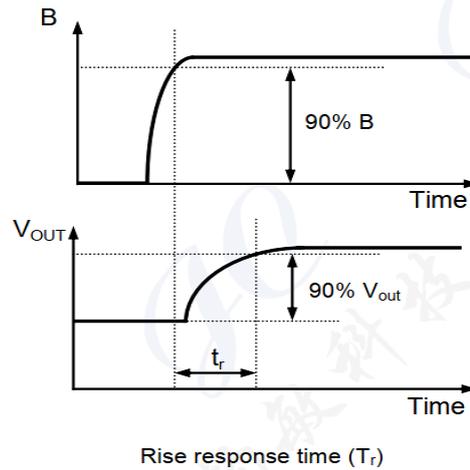


Figure 4. Definition of response time

5. Output Saturation Voltage $V_{out-SatH}$ and $V_{out-SatL}$.

Output saturation voltage is defined as the saturated output at a fixed output current. $V_{out-SatH}$ is defined as the chip's output voltage when the output current is -2 or 0.5mA in the positive magnetic field, and $V_{out-SatL}$ is the chip's output voltage when the output current is -2 or 0.5mA in the negative magnetic field.

